

What is claimed is:

1. A semiconductor light emitting device comprising:
a semiconductor light emitting portion;
a front surface electrode provided on one side of the semiconductor light emitting portion;
an electrically conductive substrate provided on the other side of the semiconductor light emitting portion, the electrically conductive substrate being transparent to a wavelength of light emitted from the semiconductor light emitting portion;
a rear surface electrode having a pattern in ohmic contact with a first region of a back surface of the electrically conductive substrate opposite from the semiconductor light emitting portion; and
a rear surface insulation layer covering a second region of the back surface of the electrically conductive substrate other than the first region, the rear surface insulation layer being transparent to the wavelength of the light emitted from the semiconductor light emitting portion.
2. A semiconductor light emitting device as set forth in claim 1, further comprising a reflection layer composed of an electrically conductive material deposited as contacting the rear surface electrode and covering the rear surface electrode and the rear surface insulation

layer, the reflection layer having a greater reflectivity with respect to the wavelength of the light emitted from the semiconductor light emitting portion than the rear surface electrode.

3. A semiconductor light emitting device as set forth in claim 1, wherein the electrically conductive substrate is a silicon carbide substrate having a dopant content controlled so that the substrate has a resistivity of $0.05\Omega\text{cm}$ to $0.5\Omega\text{cm}$.

4. A semiconductor light emitting device as set forth in claim 1, wherein the front surface electrode comprises a transparent electrode film provided in contact with the semiconductor light emitting portion and composed of an electrically conductive material transparent to the emitted light wavelength.